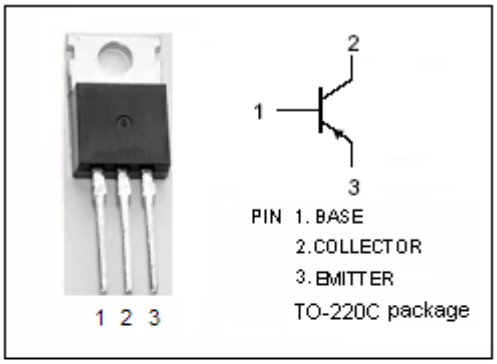
isc Silicon PNP Power Transistor MJE2901T



DESCRIPTION

- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$ = -60V(Min)
- High DC Current Gain-
  : h_{FE}= 25-100@I_C= -3A
- Complement to Type MJE2801T

APPLICATIONS

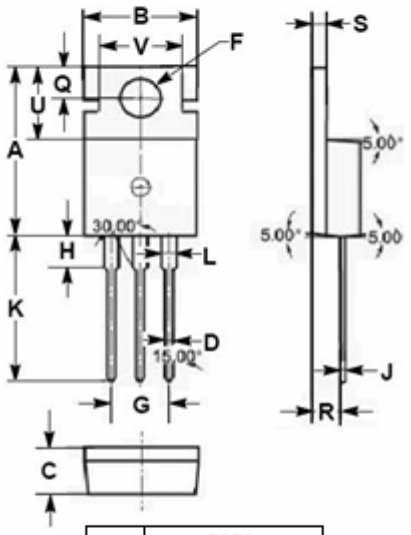
- Designed for use as an output device in complementary audio amplifiers up to 35 watts music power per channel.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-4	V
I_C	Collector Current-Continuous	-10	A
I_B	Base Current-Continuous	-5	A
P_C	Collector Power Dissipation @ T_C=25℃	75	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	1.67	℃/W



DIM	mm MIN	MAX
A	15.70	15.90
B	9.90	10.10
C	4.20	4.40
D	0.70	0.90
F	3.40	3.60
G	4.98	5.18
H	2.70	2.90
J	0.44	0.46
K	13.20	13.40
L	1.10	1.30
Q	2.70	2.90
R	2.50	2.70
S	1.29	1.31
U	6.45	6.65
V	8.66	8.86

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -200mA; I_B= 0	-60			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -4A; I_B= -0.4A			-1.1	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= -3A ; V_{CE}= -2V			-1.4	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -60V; I_E= 0 V_{CB}= -60V; I_E= 0;T_C= 150℃			-0.1 -2.0	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -4V; I_C=0			-1.0	mA
h_{FE}	DC Current Gain	I_C= -3A ; V_{CE}= -2V	25		100	